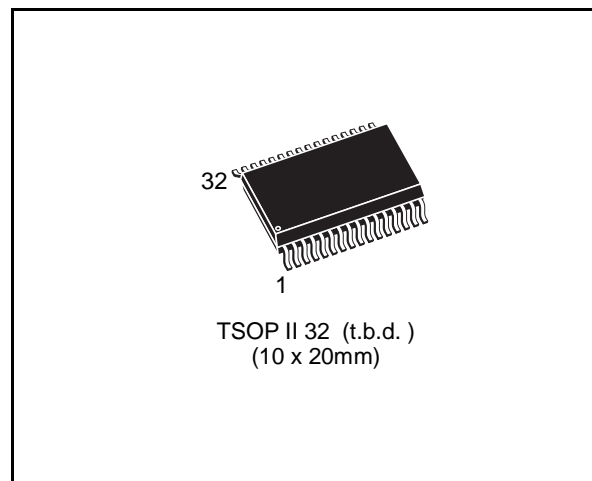




## 4 Mbit (512Kb x8) Low Power SRAM with Output Enable

PRELIMINARY DATA

- ULTRA LOW DATA RETENTION CURRENT
  - 100nA (typical)
  - 10µA (max)
- OPERATION VOLTAGE: 5V ±10%
- 512 Kbit x8 SRAM with OUTPUT ENABLE
- EQUAL CYCLE and ACCESS TIMES: 70ns
- LOW V<sub>CC</sub> DATA RETENTION: 2V
- TRI-STATE COMMON I/O
- CMOS for OPTIMUM SPEED/POWER
- AUTOMATIC POWER-DOWN WHEN DESELECTED
- INTENDED FOR USE WITH ST ZEROPOWER AND TIMEKEEPER CONTROLLERS



### DESCRIPTION

The M68Z512 is a 4 Mbit (4,194,304 bit) CMOS SRAM, organized as 524,288 words by 8 bits. The device features fully static operation requiring no external clocks or timing strobes, with equal address access and cycle times. It requires a single 5V ± 10% supply, and all inputs and outputs are TTL compatible.

This device has an automatic power-down feature, reducing the power consumption by over 99% when deselected.

The M68Z512 is available in a 32 lead TSOP II (10 x 20mm) package.

Figure 1. Logic Diagram

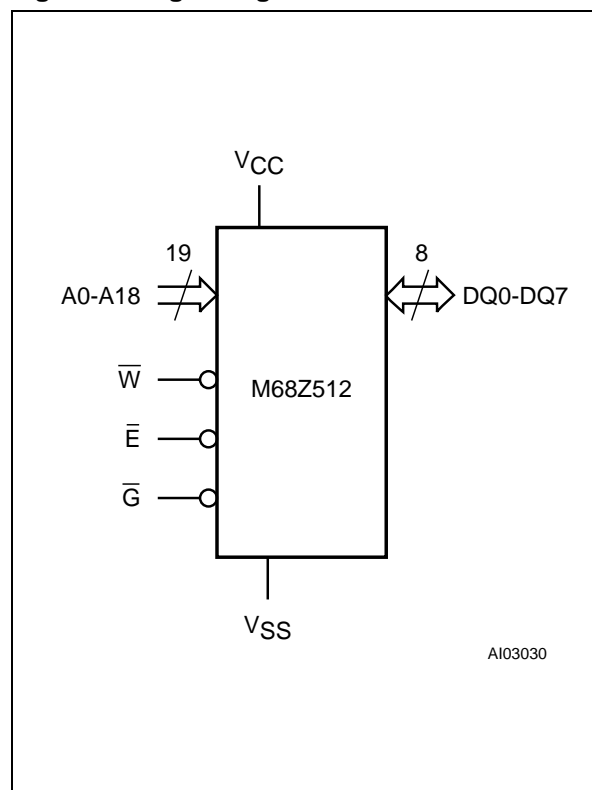


Table 1. Signal Names

A0-A18	Address Inputs
DQ0-DQ7	Data Inputs / Outputs
$\bar{E}$	Chip Enable
$\bar{G}$	Output Enable
$\bar{W}$	Write Enable
V <sub>CC</sub>	Supply Voltage
V <sub>SS</sub>	Ground

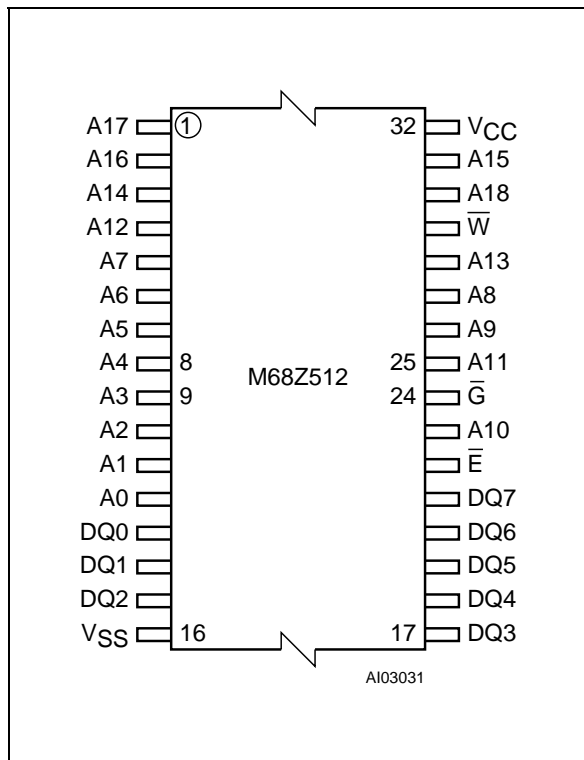
**Table 2. Absolute Maximum Ratings <sup>(1)</sup>**

Symbol	Parameter	Value	Unit
T <sub>A</sub>	Ambient Operating Temperature	0 to 70	°C
T <sub>STG</sub>	Storage Temperature	-65 to 150	°C
V <sub>IO</sub> <sup>(2)</sup>	Input or Output Voltages	-0.3 to V <sub>CC</sub> + 0.3	V
V <sub>CC</sub>	Supply Voltage	-0.3 to 7.0	V
I <sub>O</sub> <sup>(3)</sup>	Output Current	20	mA
P <sub>D</sub>	Power Dissipation	1	W

**Notes:** 1. Except for the rating "Operating Temperature Range" stresses above those listed in the Table "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality documents.

- 2. Up to a maximum operating V<sub>CC</sub> of 5.5V only.
- 3. One output at a time, not to exceed 1 second duration.

**Figure 2. TSOP Pin Connections**



**READ MODE**

The M68Z512 is in the Read mode whenever Write Enable ( $\overline{W}$ ) is High with Output Enable ( $\overline{G}$ ) Low, and Chip Enable ( $\overline{E}$ ) is asserted. This provides access to data from eight of the 4,194,304 locations in the static memory array, specified by the 19 address inputs. Valid data will be available at the eight output pins within t<sub>AVQV</sub> after the last stable address, providing  $\overline{G}$  is Low and  $\overline{E}$  is Low. If Chip Enable or Output Enable access times are not met, data access will be measured from the limiting parameter (t<sub>ELQV</sub> or t<sub>GLQV</sub>) rather than the address. Data out may be indeterminate at t<sub>ELQX</sub> and t<sub>GLQX</sub>, but data lines will always be valid at t<sub>AVQV</sub>.

**WRITE MODE**

The M68Z512 is in the Write mode whenever the  $\overline{W}$  and  $\overline{E}$  pins are Low. Either the Chip Enable input ( $\overline{E}$ ) or the Write Enable input ( $\overline{W}$ ) must be de-asserted during Address transitions for subsequent write cycles. Write begins with the concurrence of Chip Enable being active with  $\overline{W}$  low. Therefore, address setup time is referenced to Write Enable and Chip Enable as t<sub>AVWL</sub> and t<sub>AVEH</sub> respectively, and is determined by the latter occurring edge.

The Write cycle can be terminated by the earlier rising edge of  $\overline{E}$ , or  $\overline{W}$ .

**Table 3. Operating Modes**

Mode	$\bar{E}$	$\bar{W}$	$\bar{G}$	DQ0-DQ7	Power
Read	$V_{IL}$	$V_{IH}$	$V_{IH}$	Hi-Z	Active
Read	$V_{IL}$	$V_{IH}$	$V_{IL}$	Data Output	Active
Write	$V_{IL}$	$V_{IL}$	X	Data Input	Active
Deselect	$V_{IH}$	X	X	Hi-Z	Standby

Note: X =  $V_{IH}$  or  $V_{IL}$

**Table 4. AC Measurement Conditions**

Input Rise and Fall Times	$\leq 5\text{ns}$
Input Pulse Voltages	0 to 3V
Input and Output Timing Ref. Voltages	1.5V

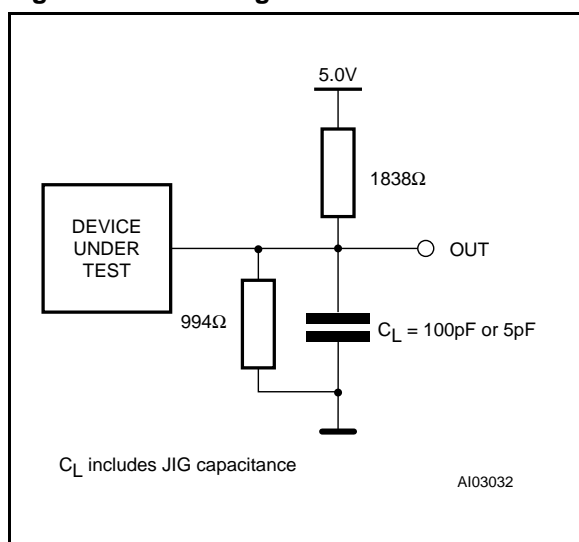
Note that Output Hi-Z is defined as the point where data is no longer driven.

If the Output is enabled ( $\bar{E}$  = Low and  $\bar{G}$  = Low), then  $\bar{W}$  will return the outputs to high impedance within  $t_{WLOZ}$  of its falling edge. Care must be taken to avoid bus contention in this type of operation. Data input must be valid for  $t_{DVWH}$  before the rising edge of Write Enable, or for  $t_{DVEH}$  before the rising edge of  $\bar{E}$ , whichever occurs first, and remain valid for  $t_{WHDX}$  or  $t_{EHDX}$ .

**OPERATIONAL MODE**

The M68Z512 has a Chip Enable power down feature which invokes an automatic standby mode whenever Chip Enable is de-asserted ( $\bar{E}$  = High). An Output Enable ( $\bar{G}$ ) signal provides a high speed tri-state control, allowing fast read/write cycles to

**Figure 4. AC Testing Load Circuit**



be achieved with the common I/O data bus. Operational modes are determined by device control inputs  $\bar{W}$  and  $\bar{E}$  as summarized in the Operating Modes table.

**Table 5. Capacitance <sup>(1)</sup>** ( $T_A = 25^\circ\text{C}$ ,  $f = 1\text{MHz}$ )

Symbol	Parameter	Test Condition	Min	Max	Unit
$C_{IN}$	Input Capacitance on all pins (except DQ)	$T_A = 25^\circ\text{C}$ , $f = 1\text{MHz}$ , $V_{CC} = 5\text{V}$		6	pF
$C_{OUT}^{(2)}$	Output Capacitance	$T_A = 25^\circ\text{C}$ , $f = 1\text{MHz}$ , $V_{CC} = 5\text{V}$		8	pF

Notes: 1. Sampled only, not 100% tested  
 2. Outputs deselected

Figure 3. Block Diagram

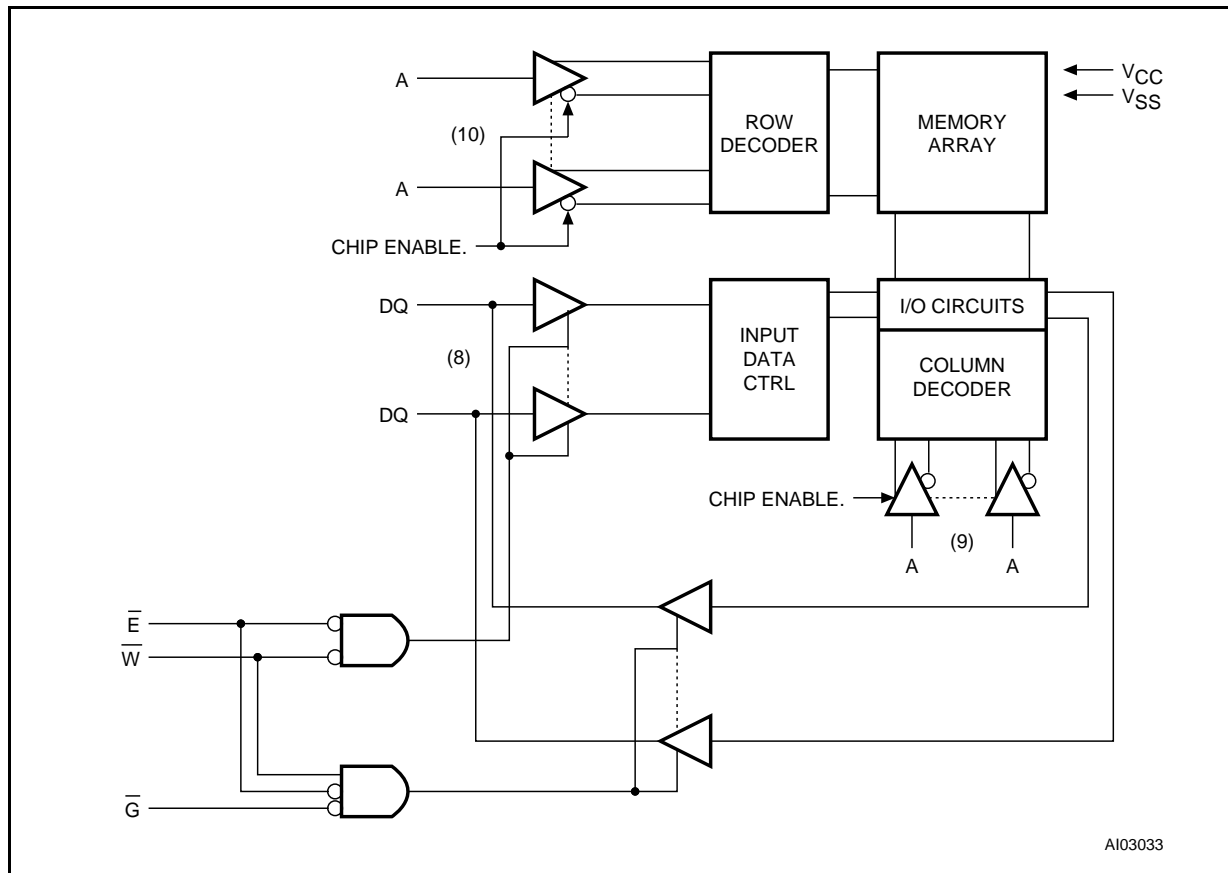


Table 6. DC Characteristics ( $T_A = 0$  to  $70$  °C;  $V_{CC} = 5V \pm 10\%$ )

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
$I_{LI}$	Input Leakage Current	$0V \leq V_{IN} \leq V_{CC}$			$\pm 1$	$\mu A$
$I_{LO}$	Output Leakage Current	$0V \leq V_{OUT} \leq V_{CC}$			$\pm 1$	$\mu A$
$I_{CC1}^{(1)}$	Supply Current	$V_{CC} = 5.5V, (-55)$			90	mA
$I_{CC2}^{(2)}$	Supply Current (Standby) TTL	$V_{CC} = 5.5V, \bar{E} = V_{IH}$			15	mA
$I_{CC3}^{(3)}$	Supply Current (Standby) CMOS	$V_{CC} = 5.5V, \bar{E} \geq V_{CC} - 0.3V, f = 0$		1.6	20	$\mu A$
$V_{IL}$	Input Low Voltage		-0.3		0.8	V
$V_{IH}$	Input High Voltage		2.2		$V_{CC} + 0.3$	V
$V_{OL}$	Output Low Voltage	$I_{OL} = 2.1mA$			0.4	V
$V_{OH}$	Output High Voltage	$I_{OH} = -1mA$	2.4			V

Notes: 1. Average AC current, Outputs open, cycling at  $t_{AVAV}$  minimum  
 2. All other Inputs at  $V_{IL} \leq 0.8V$  or  $V_{IH} \geq 2.2V$   
 3. All other Inputs at  $V_{IL} \leq 0.3V$  or  $V_{IH} \geq V_{CC} - 0.3V$

**Table 7. Read and Standby Modes AC Characteristics**  
 ( $T_A = 0$  to  $70^\circ\text{C}$ ;  $V_{CC} = 5\text{V} \pm 10\%$ )

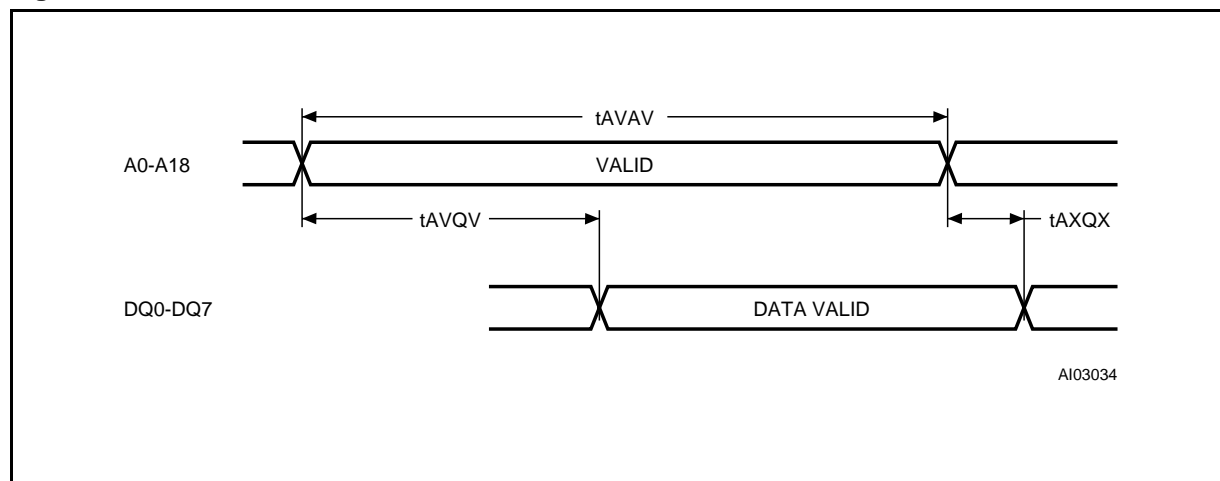
Symbol	Parameter	M68Z512		Unit
		-70		
		Min	Max	
$t_{AVAV}$	Read Cycle Time	70		ns
$t_{AVQV}^{(1)}$	Address Valid to Output Valid		70	ns
$t_{ELQV}^{(1)}$	Chip Enable Low to Output Valid		70	ns
$t_{GLQV}^{(1)}$	Output Enable Low to Output Valid		35	ns
$t_{ELQX}^{(3)}$	Chip Enable Low to Output Transition	10		ns
$t_{GLQX}^{(3)}$	Output Enable Low to Output Transition	5		ns
$t_{EHQZ}^{(2,3)}$	Chip Enable High to Output Hi-Z		25	ns
$t_{GHQZ}^{(2,3)}$	Output Enable High to Output Hi-Z		25	ns
$t_{AXQX}^{(1)}$	Address Transition to Output Transition	10		ns
$t_{PU}$	Chip Enable Low to Power Up	0		ns
$t_{PD}$	Chip Enable High to Power Down		70	ns

Notes: 1.  $C_L = 100\text{pF}$  (see Figure 4)

2.  $C_L = 5\text{pF}$  (see Figure 4)

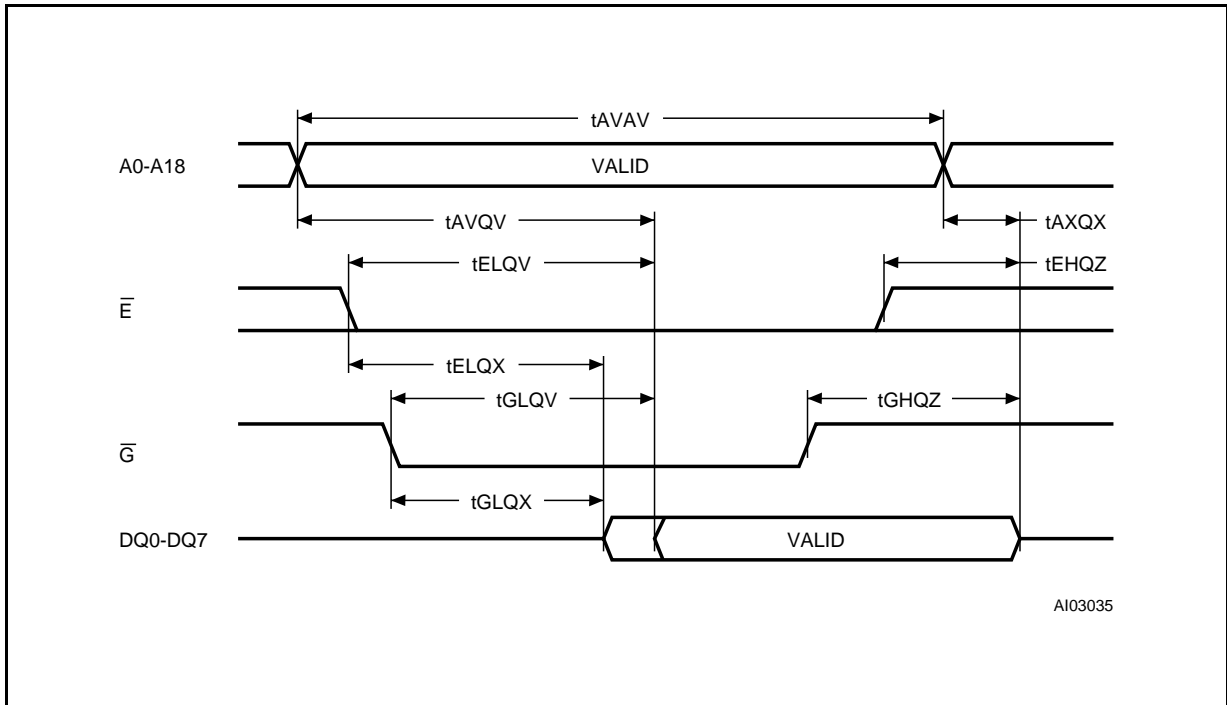
3. At any given temperature and voltage condition,  $t_{EHQZ}$  is less than  $t_{ELQX}$  and  $t_{GHQZ}$  is less than  $t_{GLQX}$  for any given device.

**Figure 5. Address Controlled, Read Mode AC Waveforms**



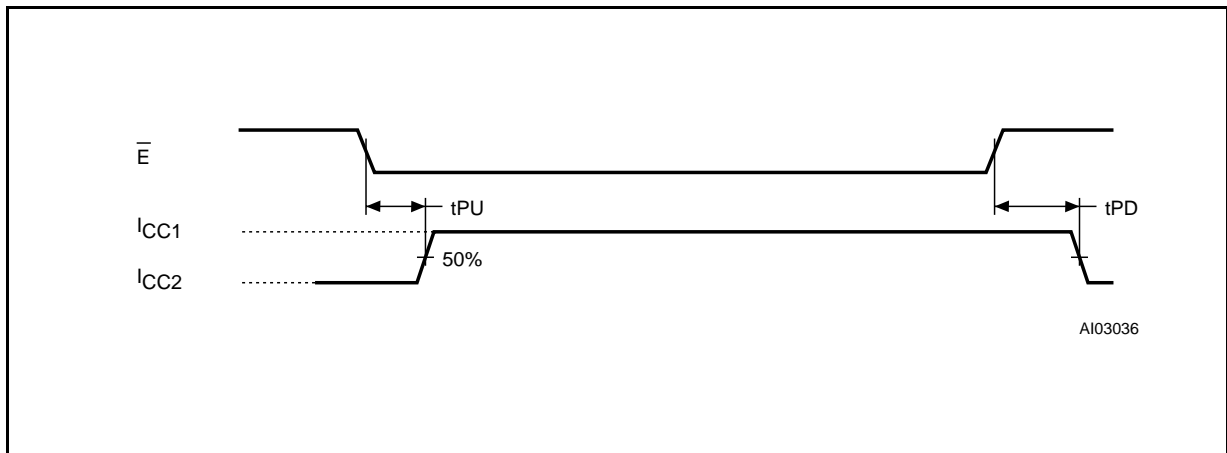
Note:  $\overline{E1}$  = Low,  $E2$  = High,  $\overline{G}$  = Low,  $\overline{W}$  = High

Figure 6. Chip Enable or Output Enable Controlled, Read Mode AC Waveforms



Note: Write Enable ( $\bar{W}$ ) = High

Figure 7. Standby Mode AC Waveforms



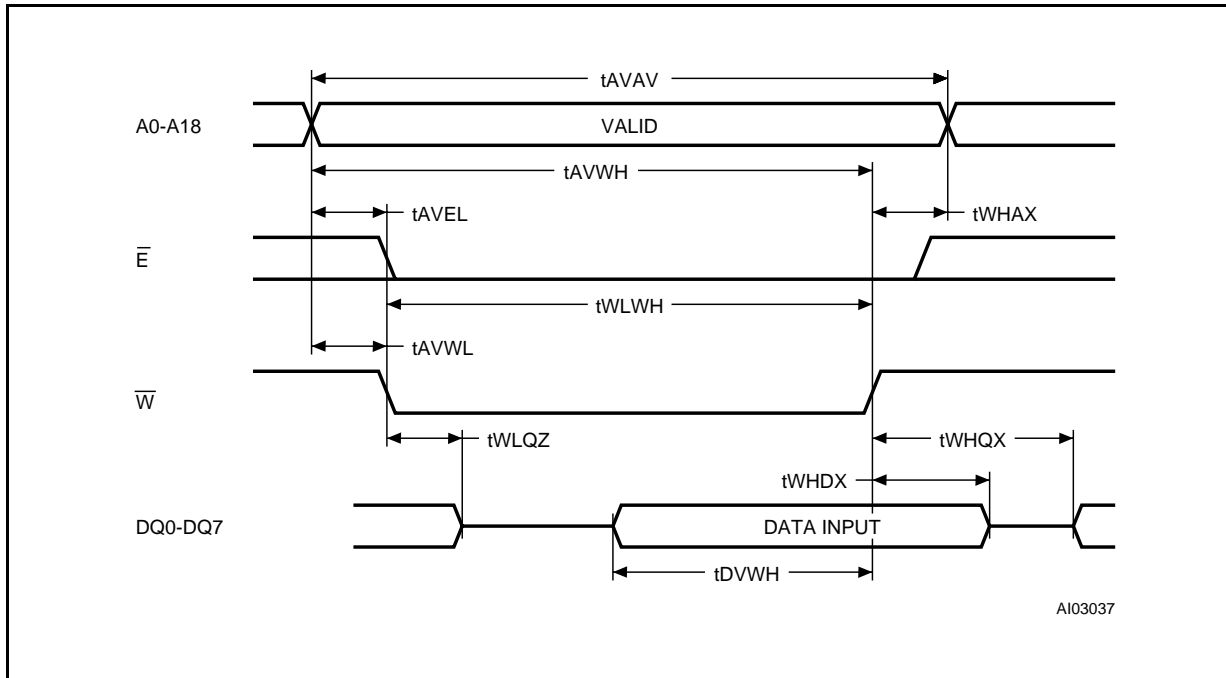
**Table 8. Write Mode AC Characteristics** ( $T_A = 0$  to  $70^\circ\text{C}$ ;  $V_{CC} = 5V \pm 10\%$ )

Symbol	Parameter	M68Z512		Unit
		-70		
		Min	Max	
$t_{AVAV}$	Write Cycle Time	70		ns
$t_{AVWL}$	Address Valid to Write Enable Low	0		ns
$t_{AVWH}$	Address Valid to Write Enable High	60		ns
$t_{AVEH}$	Address Valid to Chip Enable High	60		ns
$t_{WLWH}$	Write Enable Pulse Width	55		ns
$t_{WHAX}$	Write Enable High to Address Transition	0		ns
$t_{WHDX}$	Write Enable High to Input Transition	0		ns
$t_{WHQX}^{(2)}$	Write Enable High to Output Transition	5		ns
$t_{WLQZ}^{(1,2)}$	Write Enable Low to Output Hi-Z		25	ns
$t_{AVEL}$	Address Valid to Chip Enable Low	0		ns
$t_{ELEH}$	Chip Enable Low to Chip Enable High	45		ns
$t_{EHAX}$	Chip Enable High to Address Transition	0		ns
$t_{DVWH}$	Input Valid to Write Enable High	25		ns
$t_{DVEH}$	Input Valid to Chip Enable High	25		ns

**Note:** 1.  $C_L = 5\text{pF}$  (see Figure 4)

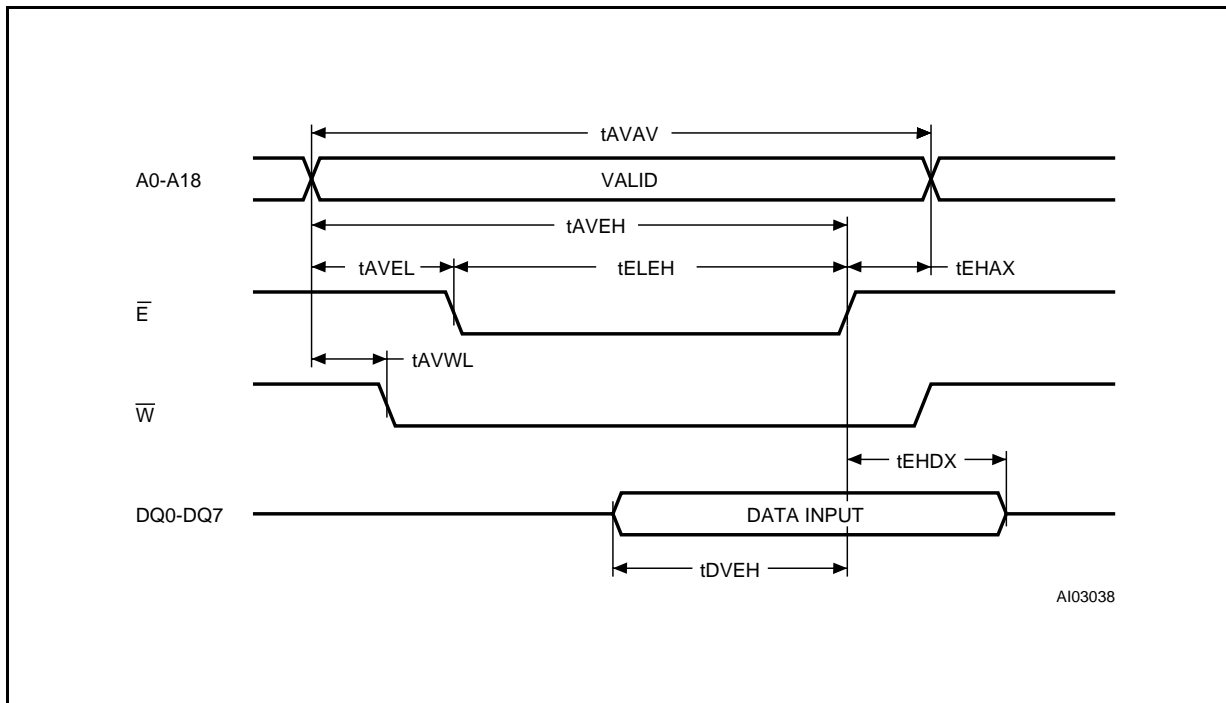
2. At any given temperature and voltage condition,  $t_{WLQZ}$  is less than  $t_{WHQX}$  for any given device.

Figure 8. Write Enable Controlled, Write AC Waveforms



Note: Output Enable ( $\bar{G}$ ) = Low

Figure 9. Chip Enable Controlled, Write AC Waveforms (1,2)



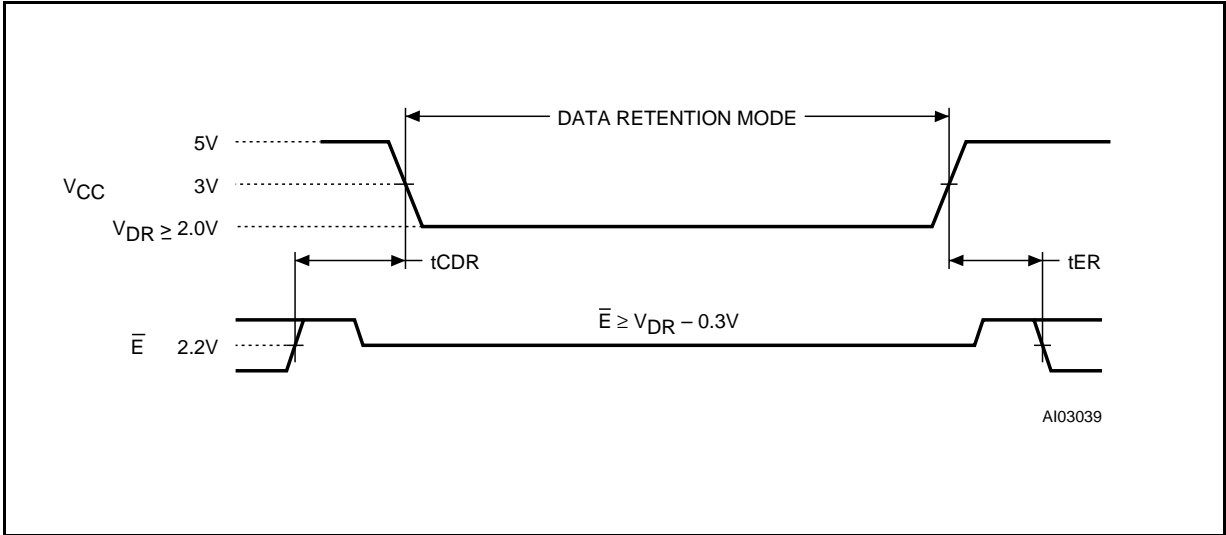
Notes: 1. Output Enable ( $\bar{G}$ ) = High  
 2. If  $\bar{E}$  goes High with  $\bar{W}$  high, the output remains in a high-impedance state.

**Table 9. Low V<sub>CC</sub> Data Retention Characteristics**  
(T<sub>A</sub> = 0 to 70°C)

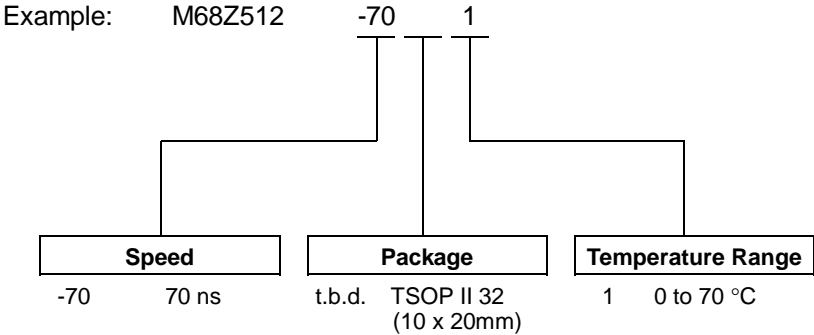
Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
I <sub>CCDR</sub> <sup>(1)</sup>	Supply Current (Data Retention)	V <sub>CC</sub> = 3V, $\bar{E} \geq V_{CC} - 0.3V$		0.1	10	μA
V <sub>DR</sub>	Supply Voltage (Data Retention)	$\bar{E} \geq V_{CC} - 0.3V$ or $E2 \leq 0.3V, f = 0$	2			V
t <sub>CDR</sub>	Chip Disable to Power Down	$\bar{E} \geq V_{CC} - 0.3V$ or $E2 \leq 0.3V, f = 0$	0			ns
t <sub>ER</sub> <sup>(2)</sup>	Operation Recovery Time		t <sub>AVAV</sub>			ns

**Note:** 1. Typical condition: T<sub>A</sub> = 25°C  
 2. See Figure 10 for measurement points. Guaranteed but not tested. t<sub>AVAV</sub> is Read cycle time.

**Figure 10. Low V<sub>CC</sub> Data Retention AC Waveforms**



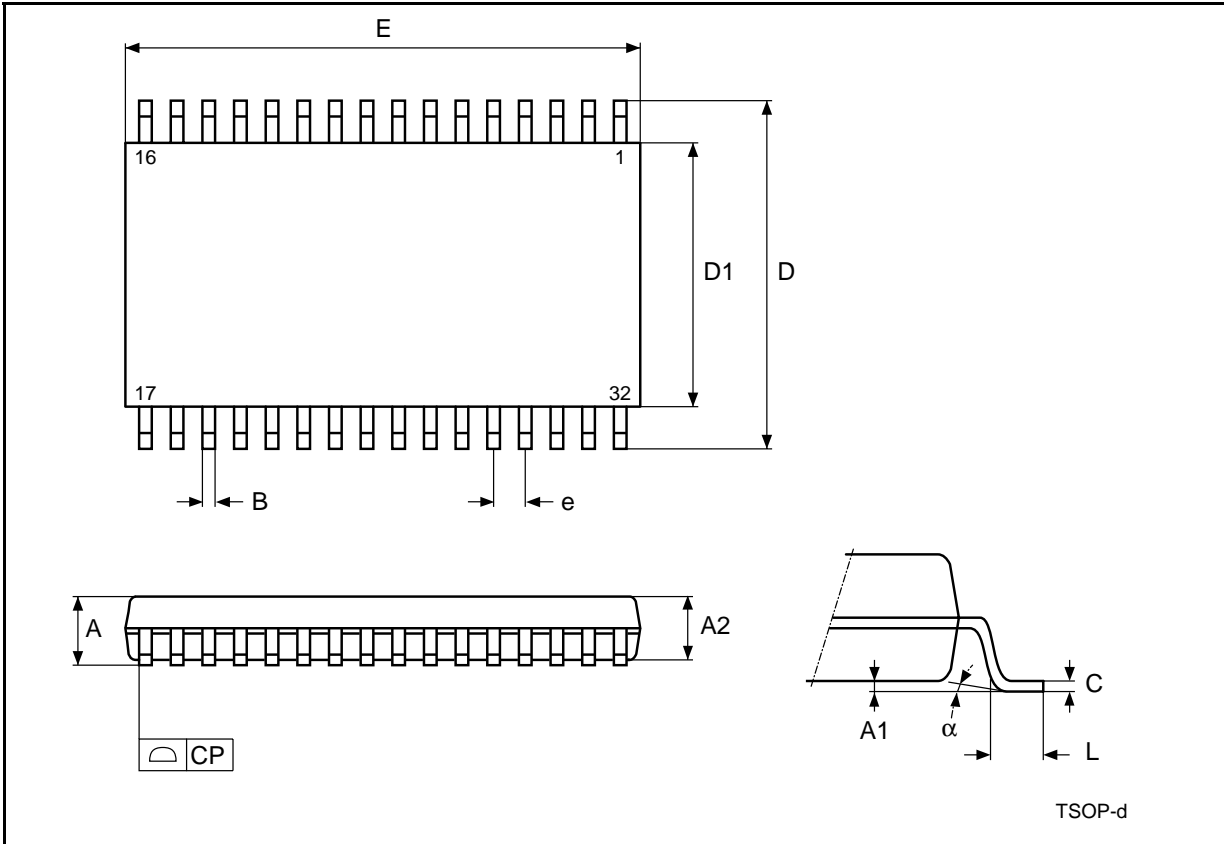
**ORDERING INFORMATION SCHEME**



For a list of available options (Speed, Package, etc...) or for further information on any aspect of this device, please contact the STMicroelectronics Sales Office nearest to you.

**TSOP II 32 - 32 lead Plastic Thin Small Outline II (10 x 20mm)**

Symbol	mm			inches		
	Typ	Min	Max	Typ	Min	Max
A			1.20			0.047
A1		0.05	0.15		0.002	0.007
A2		0.95	1.05		0.037	0.041
B		0.30	0.52		0.012	0.020
C		0.12	0.21		0.004	0.008
D		11.56	11.96		0.455	0.471
D1		10.03	10.29		0.395	0.405
E		20.82	21.08		0.820	0.830
e	1.27	-	-	0.050	-	-
L		0.40	0.60		0.016	0.024
a		0°	5°		0°	5°
N	32			32		
CP			0.10			0.004



Drawing is not to scale



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